

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hiroshi OJI	Art Unit: 2818
Application No.: 10/572,730	
Confirmation No.: 6903	Examiner: A. Huynh
Filing or 371(c) Date: March 21, 2006	
Title: SEMICONDUCTOR DEVICE HAVING HIGH-K GATE DIELECTRIC LAYER AND METHOD FOR MANUFACTURING THE SAME	

**AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated January 2, 2009, please amend the above-identified application as follows:

☐ **Amendments to the Specification** begin on page      of this paper.

☒ **Amendments to the Claims** are reflected in the listing of the claims which begins on page 2 of this paper.

☐ **Amendments to the Drawings** begin on page      of this paper and include an attached replacement sheet. An **Appendix** including the amended drawing figures is attached following page      of this paper.

☒ **Remarks/Arguments** begin on page 4 of this paper.

Please note, if a box is not checked, then no corresponding amendment is being made.